

# BUK95/96/9E04-40A

TrenchMOS™ logic level FET

Rev. 01 — 24 October 2001

Product data

## 1. Description

N-channel enhancement mode field-effect power transistor in a plastic package using TrenchMOS™ technology, featuring very low on-state resistance.

Product availability:

BUK9504-40A in SOT78 (TO-220AB); BUK9604-40A in SOT404 (D 2-PAK);  
BUK9E04-40A in SOT226 (I<sup>2</sup>-PAK).

## 2. Features

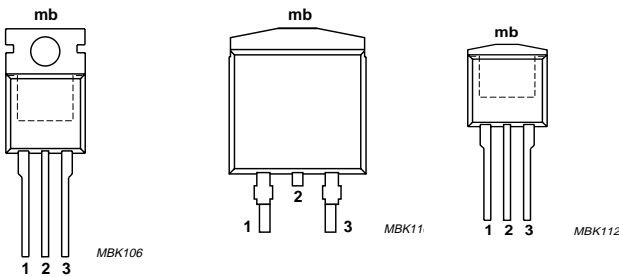
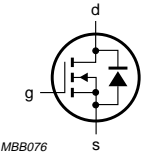
- TrenchMOS™ technology
- Q101 compliant
- 175 °C rated
- Logic level compatible.

## 3. Applications

- Automotive and general purpose power switching:
  - ◆ 12 V loads
  - ◆ Motors, lamps and solenoids.

## 4. Pinning information

Table 1: Pinning - SOT78, SOT404, SOT226 simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	drain (d) <span style="color: red;">[1]</span>		
3	source (s)		
mb	mounting base, connected to drain (d)		
		SOT78 (TO-220AB)    SOT404 (D <sup>2</sup> -PAK)    SOT226 (I <sup>2</sup> -PAK)	

[1] It is not possible to make connection to pin 2 of the SOT404 package.

## 5. Quick reference data

**Table 2: Quick reference data**

Symbol	Parameter	Conditions	Typ	Max	Unit
$V_{DS}$	drain-source voltage (DC)		-	40	V
$I_D$	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V}$	[1] -	198	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	-	300	W
$T_j$	junction temperature		-	175	°C
$R_{DSon}$	drain-source on-state resistance	$T_j = 25\text{ °C}; V_{GS} = 5\text{ V}; I_D = 25\text{ A}$	3.5	4.4	mΩ
		$T_j = 25\text{ °C}; V_{GS} = 4.3\text{ V}; I_D = 25\text{ A}$	3.7	5.9	mΩ
		$T_j = 25\text{ °C}; V_{GS} = 10\text{ V}; I_D = 25\text{ A}$	2.9	4	mΩ

## 6. Limiting values

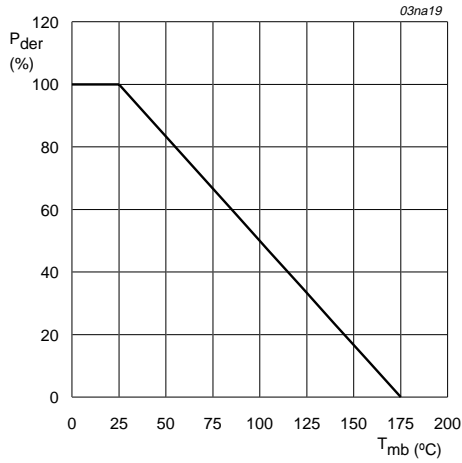
**Table 3: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage (DC)		-	40	V
$V_{DGR}$	drain-gate voltage (DC)	$R_{GS} = 20\text{ k}\Omega$	-	40	V
$V_{GS}$	gate-source voltage (DC)		-	±15	V
$I_D$	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V};$ Figure 2 and 3	[1] -	198	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 5\text{ V};$ Figure 2	[2] -	75	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 5\text{ V};$ Figure 2	[2] -	75	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	794	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ Figure 1	-	300	W
$T_{stg}$	storage temperature		-55	+175	°C
$T_j$	operating junction temperature		-55	+175	°C
<b>Source-drain diode</b>					
$I_{DR}$	reverse drain current (DC)	$T_{mb} = 25\text{ °C}$	[1] -	198	A
			[2] -	75	A
$I_{DRM}$	pulsed reverse drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	794	A
<b>Avalanche ruggedness</b>					
$W_{DSS}$	non-repetitive avalanche energy	unclamped inductive load; $I_D = 75\text{ A};$ $V_{DS} \leq 40\text{ V}; V_{GS} = 5\text{ V}; R_{GS} = 50\text{ }\Omega;$ starting $T_{mb} = 25\text{ °C}$	-	1.6	J

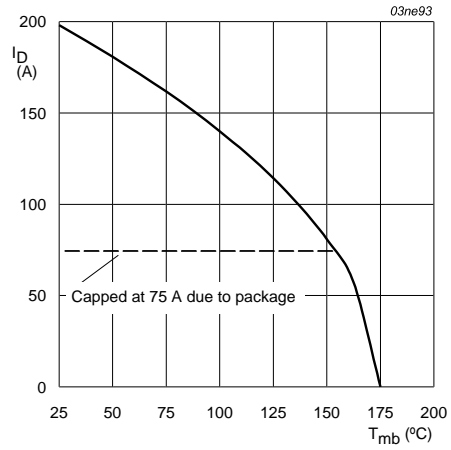
[1] Current is limited by power dissipation chip rating

[2] Continuous current is limited by package



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

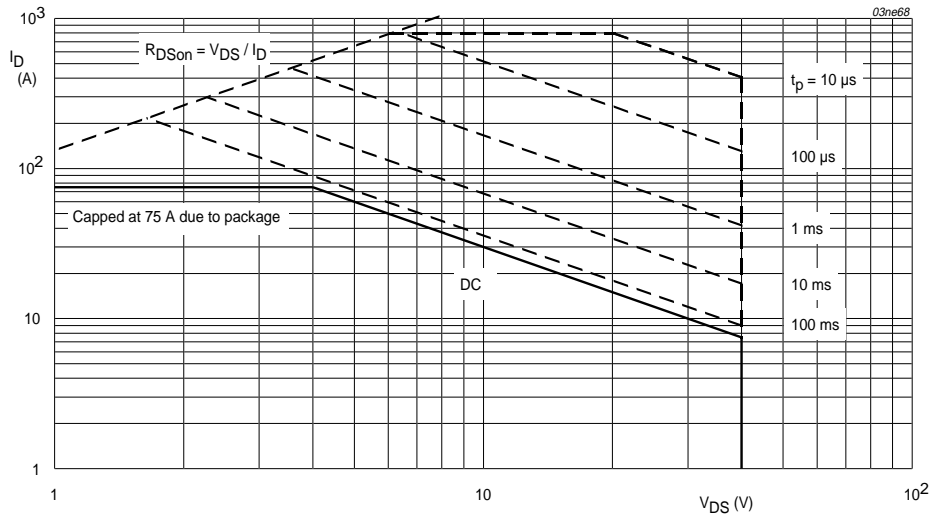
Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$$V_{GS} \geq 4.5 \text{ V}$$

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Continuous drain current as a function of mounting base temperature.



T<sub>mb</sub> = 25 °C; I<sub>DM</sub> single pulse.

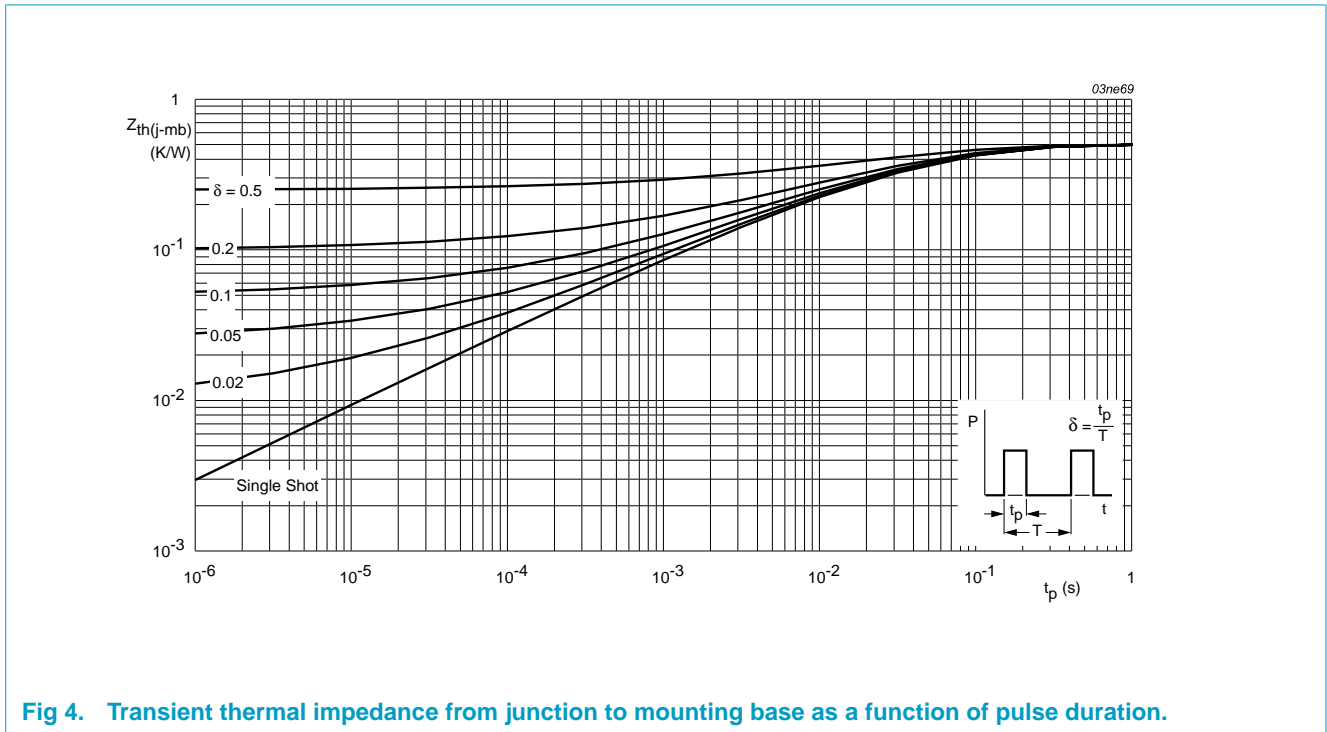
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

## 7. Thermal characteristics

**Table 4: Thermal characteristics**

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air; SOT78 and SOT226 packages	60	K/W
		mounted on printed circuit board; minimum footprint; SOT404 package	50	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	0.5	K/W

### 7.1 Transient thermal impedance



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.**

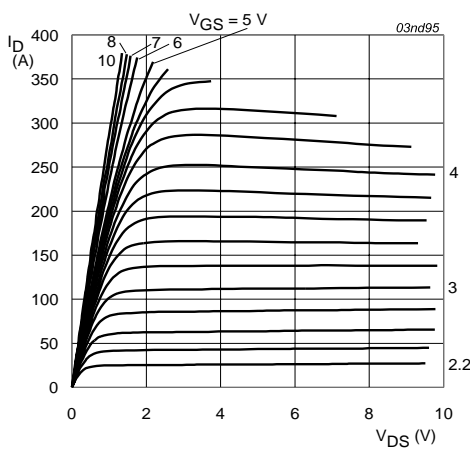
## 8. Characteristics

**Table 5: Characteristics**
 $T_j = 25\text{ °C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}$ ; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	40	-	-	V
		$T_j = -55\text{ °C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; <b>Figure 9</b> $T_j = 25\text{ °C}$	1	1.5	2	V
		$T_j = 175\text{ °C}$	0.5	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.3	V
$I_{DSS}$	drain-source leakage current	$V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	-	0.05	10	$\mu\text{A}$
		$T_j = 175\text{ °C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate-source leakage current	$V_{GS} = \pm 10\text{ V}$ ; $V_{DS} = 0\text{ V}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; <b>Figure 7 and 8</b> $T_j = 25\text{ °C}$	-	3.5	4.4	m $\Omega$
		$T_j = 175\text{ °C}$	-	-	8.3	m $\Omega$
		$V_{GS} = 4.3\text{ V}$ ; $I_D = 25\text{ A}$	-	3.7	5.9	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$	-	2.9	4	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{g(tot)}$	total gate charge	$V_{GS} = 5\text{ V}$ ; $V_{DD} = 32\text{ V}$ ; $I_D = 25\text{ A}$ ; <b>Figure 14</b>	-	128	-	nC
$Q_{gs}$	gate-to-source charge		-	13	-	nC
$Q_{gd}$	gate-to-drain (Miller) charge		-	56	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ; <b>Figure 12</b>	-	6200	8260	pF
$C_{oss}$	output capacitance		-	1040	1250	pF
$C_{rss}$	reverse transfer capacitance		-	680	940	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 30\text{ V}$ ; $R_L = 1.2\text{ }\Omega$ ; $V_{GS} = 5\text{ V}$ ; $R_G = 10\text{ }\Omega$	-	62	-	ns
$t_r$	rise time		-	309	-	ns
$t_{d(off)}$	turn-off delay time		-	365	-	ns
$t_f$	fall time		-	306	-	ns
$L_d$	internal drain inductance	from drain lead 6 mm from package to centre of die	-	4.5	-	nH
		from contact screw on mounting base to centre of die SOT78	-	3.5	-	nH
		from upper edge of drain mounting base to centre of die SOT404 / SOT226	-	2.5	-	nH
$L_s$	internal source inductance	from source lead to source bond pad	-	7.5	-	nH

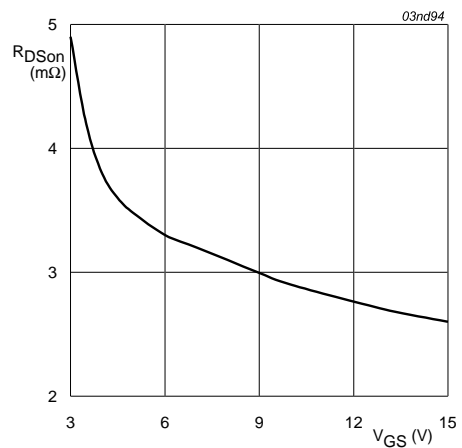
**Table 5: Characteristics...continued**  
 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain (diode forward) voltage	$I_S = 40\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; Figure 15	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$	-	260	-	ns
$Q_r$	recovered charge	$V_{GS} = -10\text{ V}$ ; $V_{DS} = 30\text{ V}$	-	531	-	nC



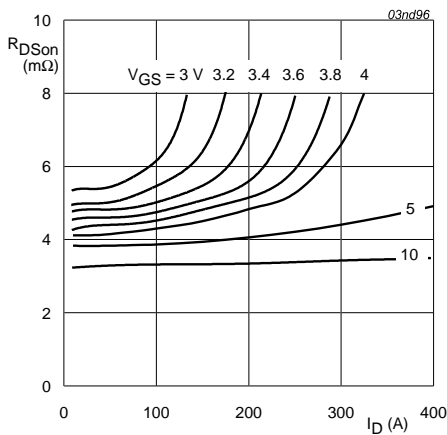
$T_j = 25\text{ }^\circ\text{C}$ ;  $t_p = 300\text{ }\mu\text{s}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.**



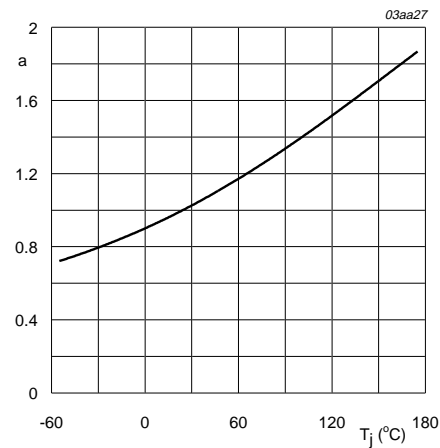
$T_j = 25\text{ }^\circ\text{C}$ ;  $I_D = 25\text{ A}$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.**



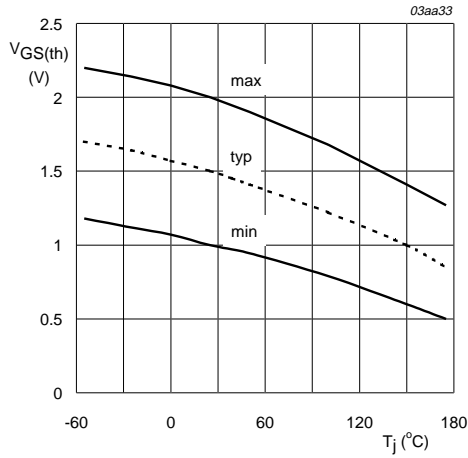
$T_j = 25\text{ }^\circ\text{C}$

**Fig 7. Drain-source on-state resistance as a function of drain current; typical values.**



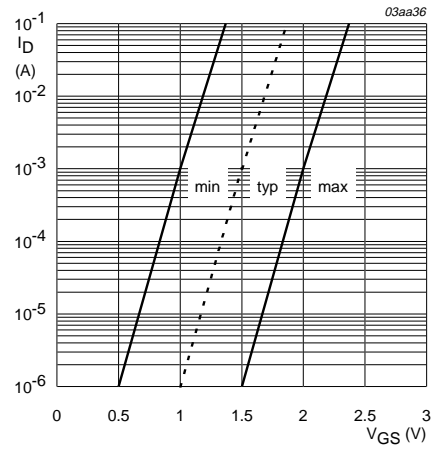
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.**



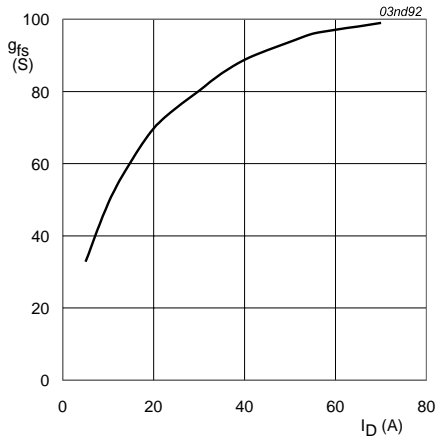
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig 9. Gate-source threshold voltage as a function of junction temperature.**



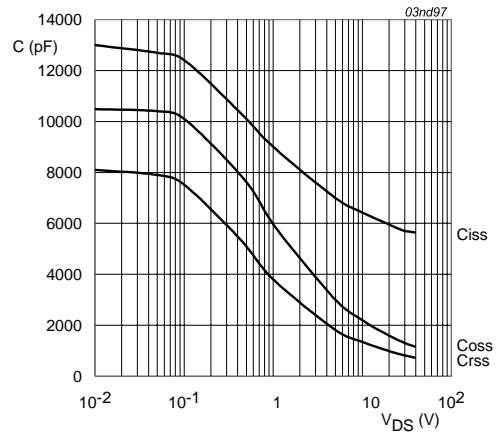
$T_j = 25 \text{ }^{\circ}C; V_{DS} = V_{GS}$

**Fig 10. Sub-threshold drain current as a function of gate-source voltage.**



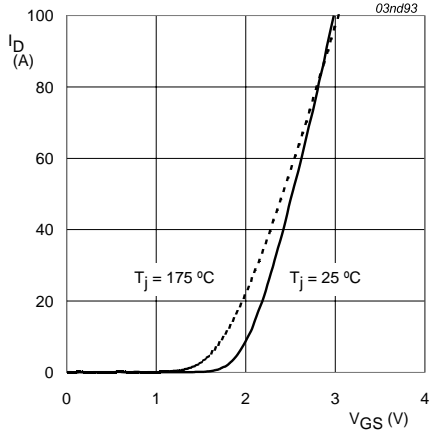
$T_j = 25 \text{ }^{\circ}C; V_{DS} = 25 \text{ V}$

**Fig 11. Forward transconductance as a function of drain current; typical values.**



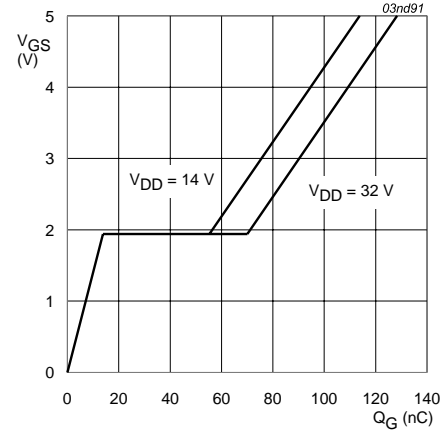
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.**



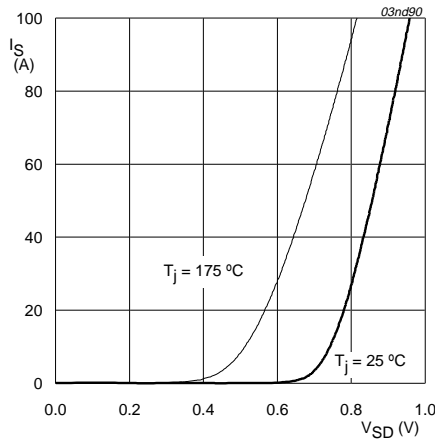
$V_{DS} = 25 \text{ V}$

**Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.**



$T_j = 25 \text{ °C}; I_D = 25 \text{ A}$

**Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.**



$V_{GS} = 0 \text{ V}$

**Fig 15. Reverse diode current as a function of reverse diode voltage; typical values.**



9. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



Fig 16. SOT78 (TO-220AB).

Plastic single-ended surface mounted package (Philips version of D<sup>2</sup>-PAK); 3 leads  
(one lead cropped)

SOT404



Fig 17. SOT404 (D<sup>2</sup>-PAK).

Plastic single-ended package; low-profile 3 lead TO-220AB

SOT226

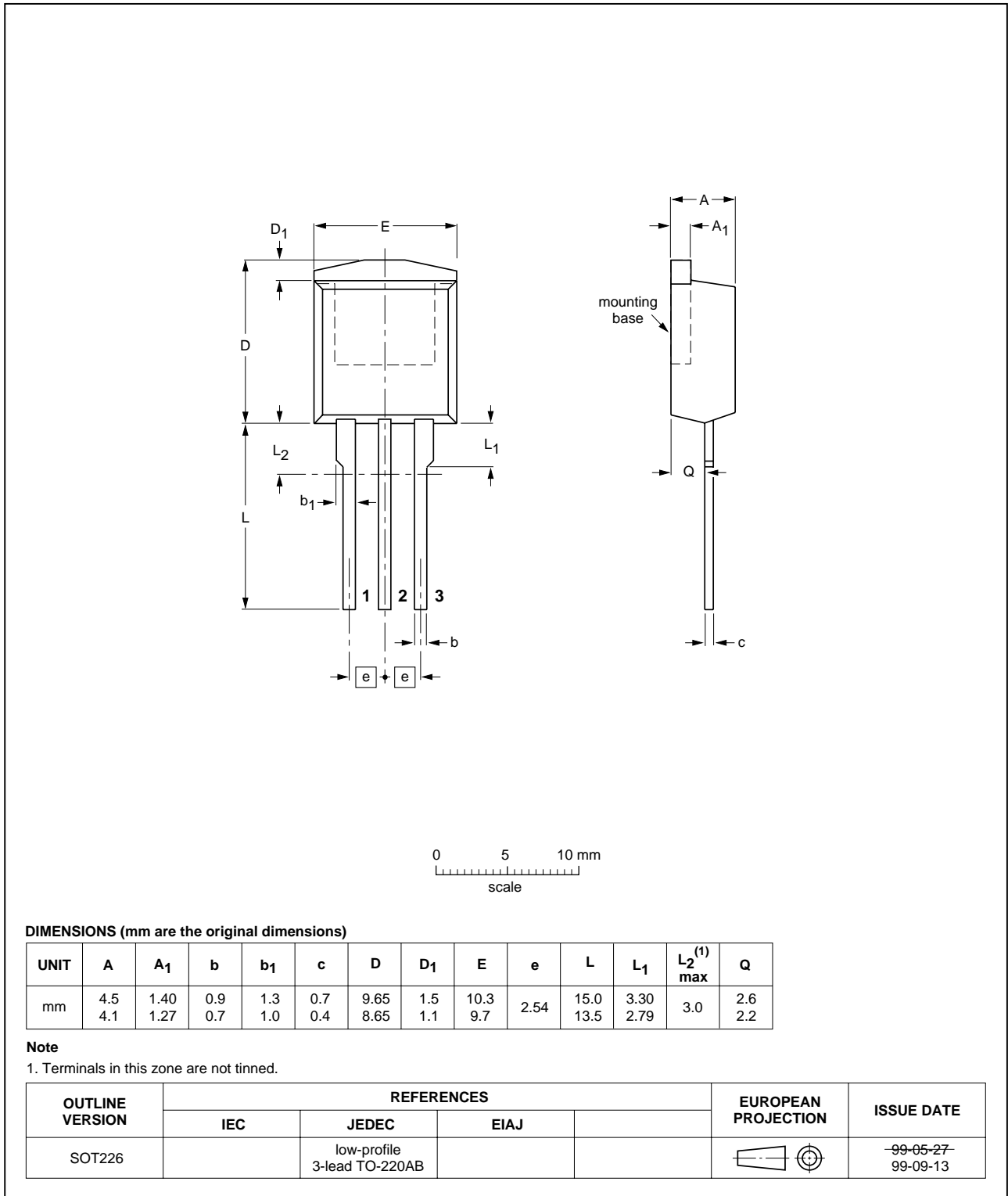
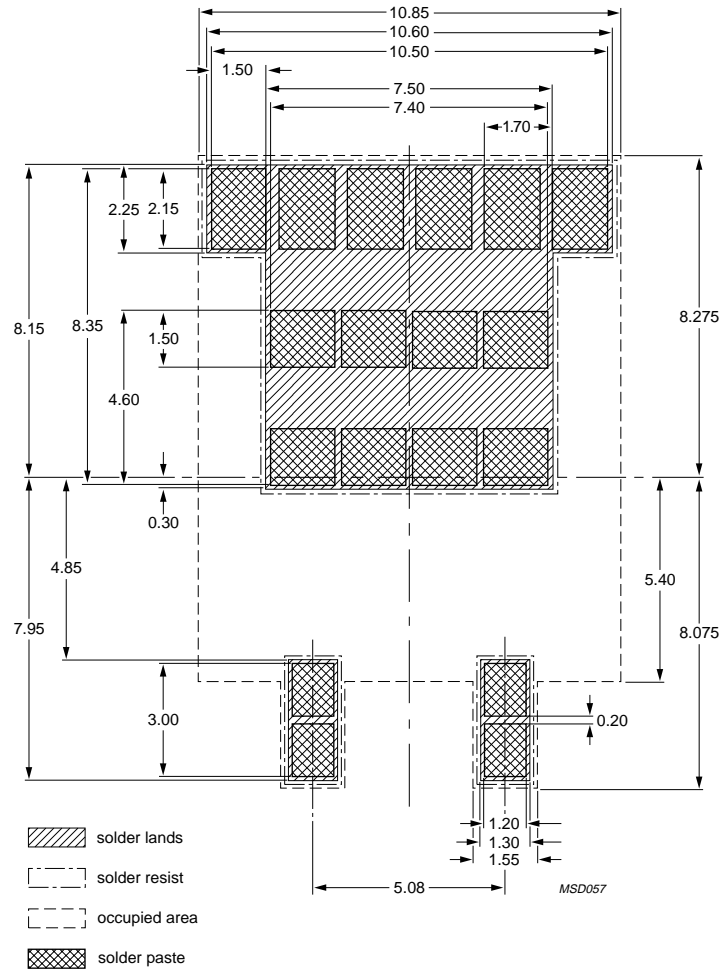


Fig 18. SOT226 (I<sup>2</sup>-PAK).

10. Soldering



Dimensions in mm.

Fig 19. Reflow soldering footprint for SOT404.

## 11. Revision history

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Table 6: Revision history

Rev	Date	CPCN	Description
01	20011024	-	Product Specification; initial version

## 12. Data sheet status

Data sheet status <sup>[1]</sup>	Product status <sup>[2]</sup>	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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